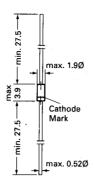
BA243A, BA244A

Silicon Epitaxial Planar Diode Switches

for electronic band-switching in radio and TV tuners in the frequency range of 50 ... 1000 MHz. The dynamic forward resistance is constant and very small over a wide range of frequency and forward current. The reverse capacitance is also small and largely independent of the reverse voltage.

These diodes are delivered taped. Details see "Taping".



Glass case JEDEC DO-35 54 A 2 according to DIN 41 880

Weight approx. 0.13 g Dimensions in mm

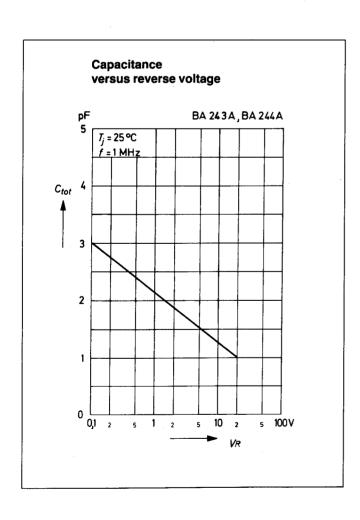
Absolute Maximum Ratings (T_a= 25°C)

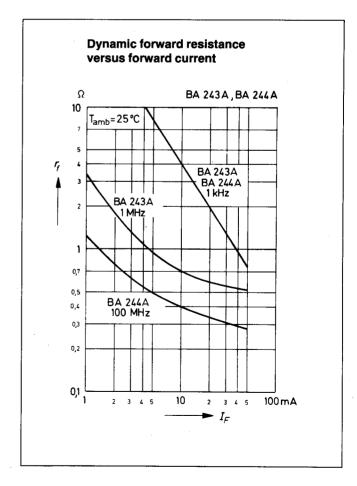
	Symbol	Value	Unit	
Reverse Voltage	V _R	35	V	
Forward Current at T _{amb} = 25 °C	I _F	100	mA	
Junction Temperature	T _i	150	°C	
Storage Temperature Range	T _s	-55 to + 150	°C	



Characteristics at T_{amb} =25 °C

	Symbol	Min.	Тур.	Max.	Unit
Forward Voltage at I _F = 100 mA	V _F	-	-	1	·V
Leakage Current at $V_R = 20 \text{ V}$ at $V_R = 15 \text{ V}$, $T_{amb} = 60 \text{ °C}$	l _R	-		50 1	nA μA
Dynamic Forward Resistance at $f = 50$ to 1000 MHz, $I_F = 10$ mA BA243A BA244A	r _f r _f		0.7 0.4	1 0.5	Ω Ω
Relative Variation of Dynamic Forward Resistance with the Variation of Forward Current in the Range of $I_F = 2$ to 40 mA	$\frac{\Delta r_{f} \cdot 100}{r_{f} \cdot \Delta l_{F}}$	-	5	-	%/mA
Capacitance at V _R = 3 V, f = 1 MHz	C _{tot}	-	-	` 1.8	pF
Relative Variation of Capacitance with the Variation of Reverse Voltage in the Range of $V_R = 7$ to 20 V, $f = 100 \text{ MHz}$	$\frac{\Delta C_{tot} \cdot 100}{C_{tot} \cdot \Delta V_{R}}$	-	. 1	-	%/V
Series Inductance across Case	L _s	-	2.5	-	nH







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